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**JUNG et al.**(10) **Pub. No.: US 2023/0403839 A1**(43) **Pub. Date: Dec. 14, 2023**(54) **SEMICONDUCTOR DEVICE AND METHOD  
FOR FABRICATING THE SAME****Publication Classification**(71) Applicant: **Samsung Electronics Co., Ltd.**,  
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(57)

**ABSTRACT**

A semiconductor device comprises a first gate structure extending in a first direction and including a first gate electrode and a first gate capping pattern, a second gate structure spaced apart from the first gate structure and extending in the first direction, and including a second gate electrode and a second gate capping pattern, an active pattern extending in a second direction, the active pattern below the second gate structure, an epitaxial pattern on one side of the second gate structure and on the active pattern, a gate contact connected to the first gate electrode, and a node contact connected to the second gate electrode and to the epitaxial pattern. An upper surface of the gate contact is at a same level as the first gate capping pattern, and an upper surface of the node contact is lower than the upper surface of the first gate capping pattern.

